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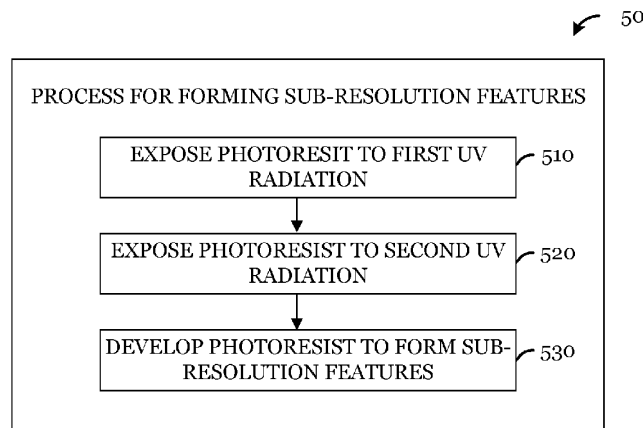


FIGURE 5A

(57) **Abstract:** A method of forming sub-resolution features that includes: exposing a photoresist layer formed over a substrate to a first ultraviolet light (UV) radiation having a first wavelength of 365 nm or longer through a mask configured to form features at a first critical dimension, the photoresist layer including first portions exposed to the first UV radiation and second portions unexposed to the first UV radiation after exposing with the first UV radiation; exposing the first portions and the second portions to a second UV radiation; and developing the photoresist layer after exposing the photoresist layer to the second UV radiation to form the sub-resolution features having a second critical dimension less than the first critical dimension.

[Continued on next page]

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